

-	416	(p\$type or n\$type) near10 concentration near5 ("10.sup.20")	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/06/12 15:47
-	2	(p\$type or n\$type) near10 concentration near5 ("10.sup.20") near10 nitride	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/06/12 15:54
-	1436	(p\$type or n\$type) near10 concentration same nitride	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/06/12 15:49
-	327	(n\$type) near10 concentration near10 (si or silicon) same nitride	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/06/12 15:50
-	3	(n\$type) near10 concentration near10 (si or silicon) same nitride and 117/\$4.ccls.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/06/12 15:51
-	137	(n\$type) near10 concentration near10 (si or silicon) same (gallium near2 nitride or gan)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/06/12 15:51
-	112	(n\$type) near10 concentration near10 (si or silicon) near10 (gallium near2 nitride or gan)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/06/12 15:52
-	3	(p\$type or n\$type) near10 concentration near5 ("10.sup.21") near10 nitride	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/06/12 15:54
-	10	(p\$type or n\$type) near10 concentration near5 ("10.sup.21") same nitride	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/06/12 15:55
-	143	(p\$type or n\$type) near10 concentration near5 ("10.sup.21")	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/06/12 15:58
-	478	(p\$type or n\$type) near10 concentration same (gallium adj nitride or gan)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/06/12 15:59
-	359	(p\$type or n\$type) near10 concentration near10 (gallium adj nitride or gan)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/06/12 16:19
-	33	((p\$type or n\$type) near10 concentration near10 (gallium adj nitride or gan)) and 117/\$4.ccls.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/06/12 16:10
-	24	(p\$type or n\$type) near10 concentration near10 (gallium adj nitride or gan) near10 more	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/06/12 16:07

-	169	(p\$type or n\$type) near10 concentration near10 (gallium adj nitride or gan) near10 high\$4	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/06/12 16:07
-	196	((p\$type or n\$type) near10 concentration near10 (gallium adj nitride or gan)) and 257\$4.ccls.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/06/12 16:11
-	2	6218269.pn.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/06/12 16:14
-	2	5578839.pn.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/06/12 16:15
-	5	(p\$type or n\$type) near10 concentration near10 (gallium adj nitride or gan) same (superlattice)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/06/12 16:19